ABSTRACT

A thermal treatment system for semiconductors comprises an outer tube made of silicon carbide, a base hermetically supporting a lower portion of the outer tube, a lid selectively opening and closing an opening formed in a central portion of the base, and a reactor wall surrounding an outer peripheral wall and the like of the outer tube and having a heater provided on an inner side, wherein an annular sealing member and an annular supporting member are interposed between the outer tube and the base, and wherein the supporting member has an effective heat transfer coefficient of 50 to 2,000 $W/(m^2 \cdot K)$.